Features

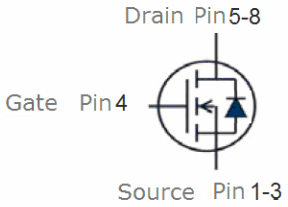
- N-Channel
- Enhancement mode
- Very low on-resistance $R_{DS(on)}$ @ V_{GS}=4.5 V
- Fast Switching
- High conversion efficiency
- Pb-free lead plating; RoHS compliant

Pb-Free RoHS HF Halogen-Free

V_{DS}	20	V
$R_{DS(on),TYP}$@ V_{GS}=4.5 V	4.5	mΩ
I_D	18	A

SOP8

Part ID	Package Type	Marking	Tape and reel information
VS2518AS	SOP8	2518AS	3000pcs/reel



Maximum ratings, at T_j=25 °C, unless otherwise specified

Symbol	Parameter		Rating	Unit
$V_{(BR)DSS}$	Drain-Source breakdown voltage		20	V
I_S	Diode continuous forward current	T_C=25°C	18	A
I_D	Continuous drain current@V_{GS}=10V	T_C=25°C	18	A
		T_A=70°C	13.5	A
I_{DM}	Pulse drain current tested ①	T_C=25°C	72	A
P_D	Maximum power dissipation	T_A=25°C	2	W
V_{GS}	Gate-Source voltage		±12	V
T_{STG} T_J	Storage and operating temperature range		-55 to 175	°C

Thermal Characteristics

Symbol	Parameter	Typical	Unit
$R_{\theta JC}$	Thermal Resistance-Junction to Case	1.6	°C/W
$R_{\theta JA}$	Thermal Resistance Junction-Ambient	62.5	°C/W

Symbol	Parameter	Condition	Min.	Typ.	Max.	Unit
Static Electrical Characteristics @ T_C = 25°C (unless otherwise stated)						
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	V_{GS}=0V I_D=250μA	20	--	--	V
I_{DSS}	Zero Gate Voltage Drain Current(Tc=25℃)	V_{DS}=16V,V_{GS}=0V	--	--	1	μA
	Zero Gate Voltage Drain Current(Tc=125℃)	V_{DS}=16V,V_{GS}=0V	--	--	100	μA
I_{GSS}	Gate-Body Leakage Current	V_{GS}=±12V,V_{DS}=0V	--	--	±100	nA
$V_{GS(TH)}$	Gate Threshold Voltage	V_{DS}=V_{GS},I_D=250μA	0.5	0.7	1.2	V
$R_{DS(ON)}$	Drain-Source On-State Resistance③	V_{GS}=10V, I_D=9A	--	4.0	5.5	mΩ
$R_{DS(ON)}$	Drain-Source On-State Resistance③	V_{GS}=4.5V, I_D=9A	--	4.5	7.0	mΩ
$R_{DS(ON)}$	Drain-Source On-State Resistance③	V_{GS}=3.3V, I_D=9A	--	5.5	8.0	mΩ
Dynamic Electrical Characteristics @ T_C= 25°C (unless otherwise stated)						
C_{iss}	Input Capacitance	V_{DS}=10V,V_{GS}=0V, f=1MHz	--	1660	--	pF
C_{oss}	Output Capacitance		--	220	--	pF
C_{rss}	Reverse Transfer Capacitance		--	160	--	pF
Q_g	Total Gate Charge	V_{DS}=10V,I_D=10A, V_{GS}=4.5V	--	30	--	nC
Q_{gs}	Gate-Source Charge		--	5	--	nC
Q_{gd}	Gate-Drain Charge		--	8	--	nC
Switching Characteristics						
$t_{d(on)}$	Turn-on Delay Time	V_{DD}=10V, I_D=10A, R_G=6.8Ω, V_{GS}=4.5V	--	13	--	nS
t_r	Turn-on Rise Time		--	15	--	nS
$t_{d(off)}$	Turn-Off Delay Time		--	20	--	nS
t_f	Turn-Off Fall Time		--	15	--	nS
Source- Drain Diode Characteristics@ T_C = 25°C (unless otherwise stated)						
V_{SD}	Forward on voltage	I_{SD}=9A,V_{GS}=0V	--	0.78	1.2	V
t_{rr}	Reverse Recovery Time	T_j=25℃,I_{sd}=9A, V_{GS}=0V di/dt=100A/μs	--	22	--	nS
Q_{rr}	Reverse Recovery Charge			13		nC

NOTE:

① Repetitive rating; pulse width limited by max. junction temperature.

② Pulse width ≤ 300μs; duty cycle≤ 2%.

Typical Characteristics

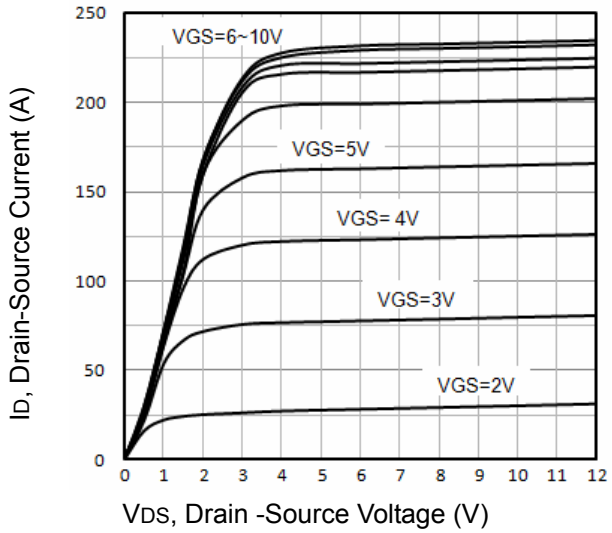


Fig1. Typical Output Characteristics

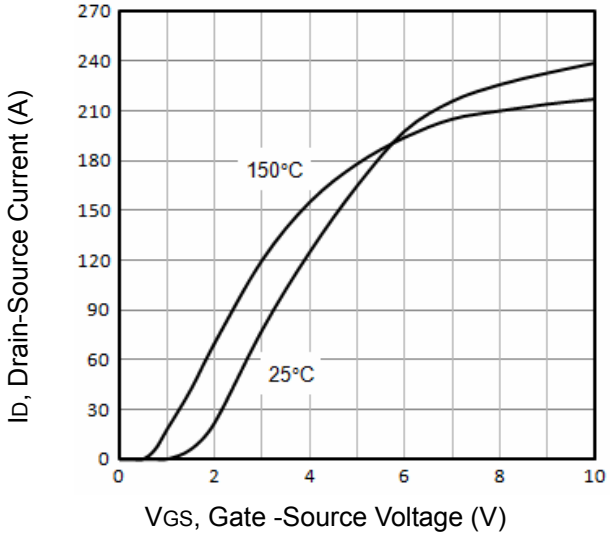


Fig2. Typical Transfer Characteristics

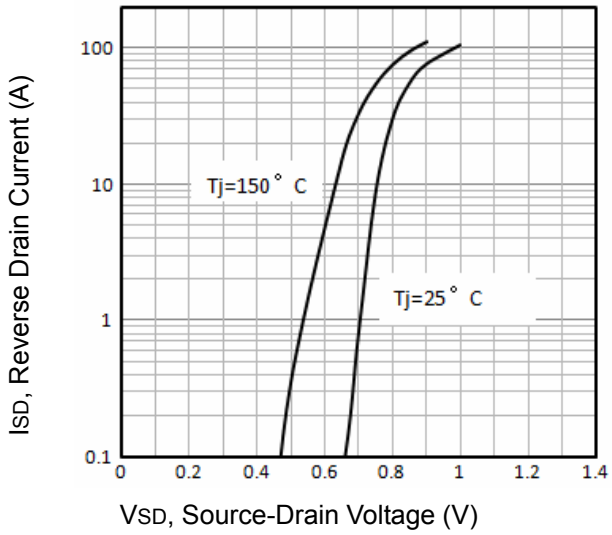


Fig3. Typical Source-Drain Diode Forward

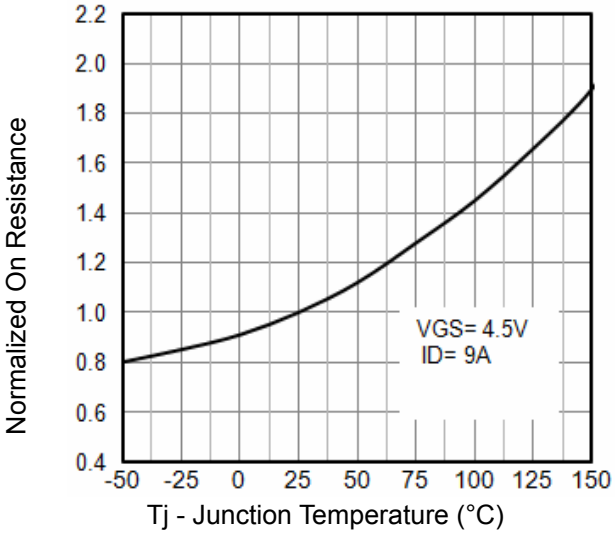


Fig4. Normalized On-Resistance Vs. Temperature

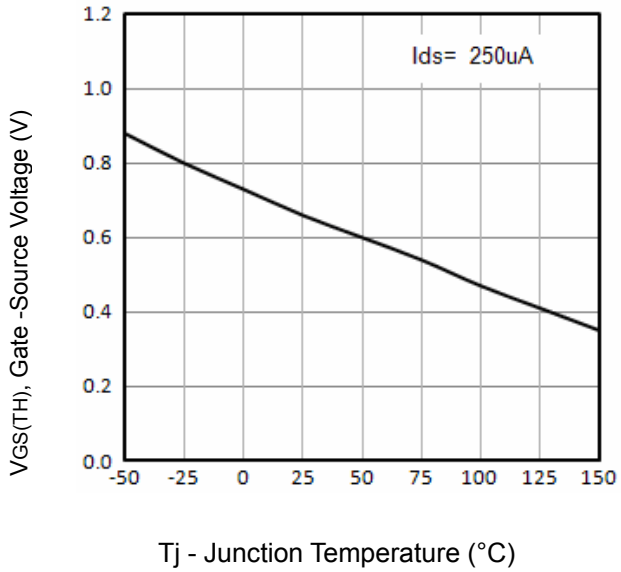


Fig5. Threshold Voltage Vs. Temperature

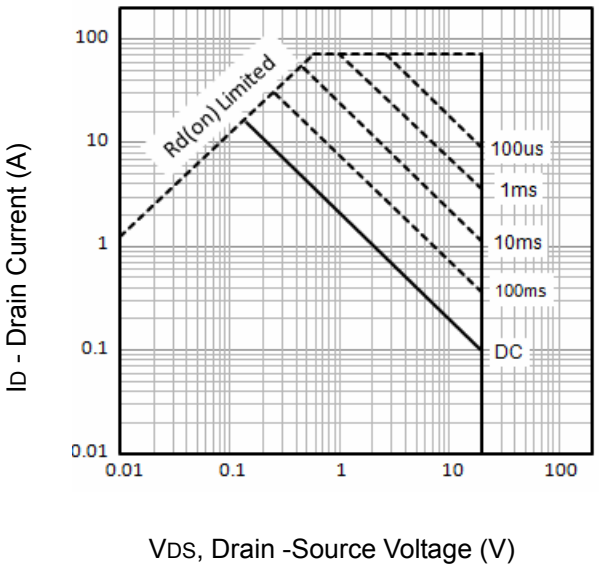


Fig6. Maximum Safe Operating Area

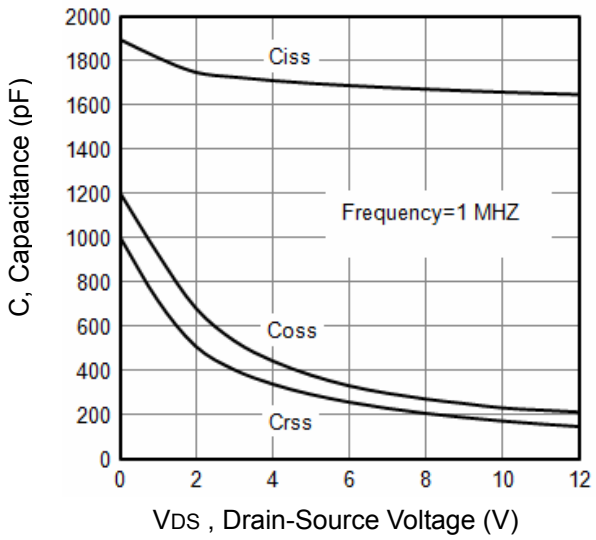


Fig7. Typical Capacitance Vs.Drain-Source Voltage

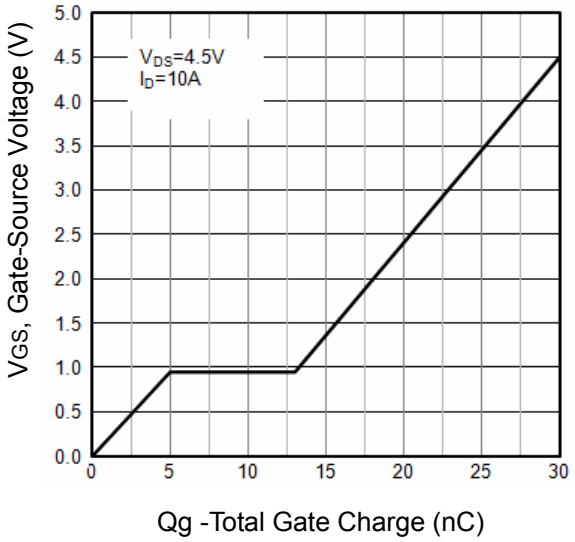
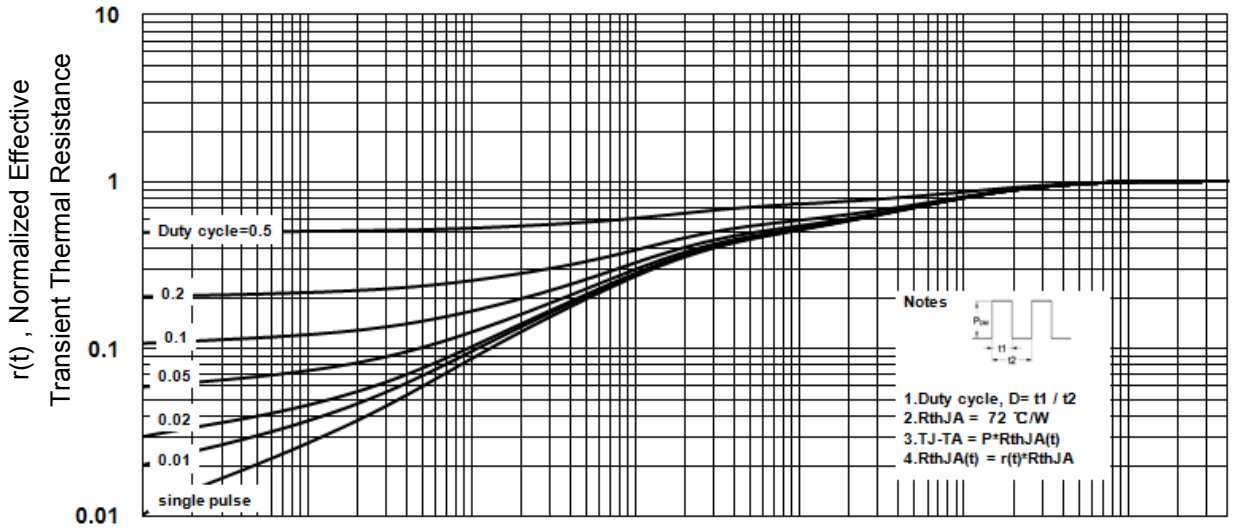


Fig8. Typical Gate Charge Vs.Gate-Source Voltage



T_1, Square Wave Pulse Duration(sec)

Fig9. **T1 ,Transient Thermal Response Curve**

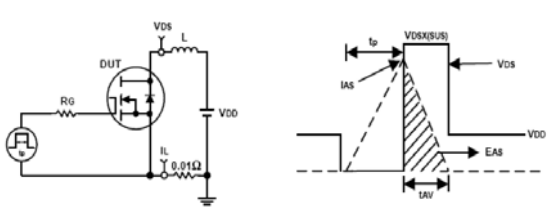


Fig10. Unclamped Inductive Test Circuit and waveforms

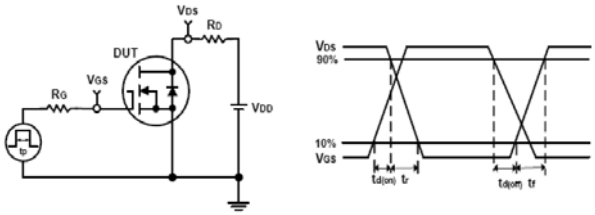
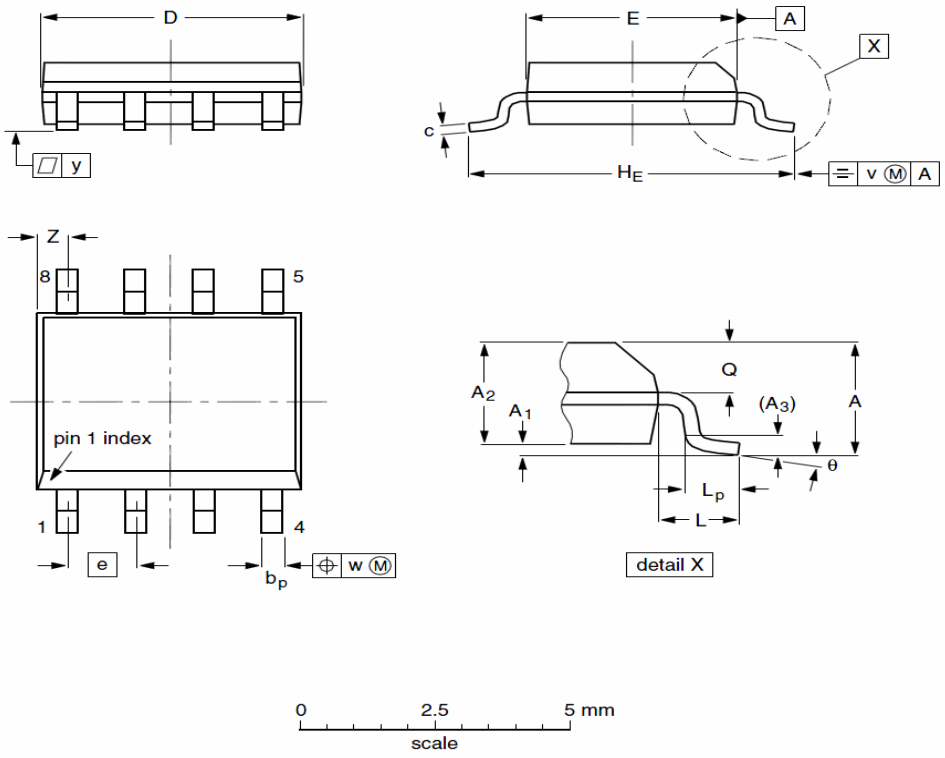


Fig11. Switching Time Test Circuit and waveforms

SOP8 Package Outline



DIMENSIONS (unit : mm)

Symbol	Min	Typ	Max	Symbol	Min	Typ	Max
A	--	1.75	--	**A_1**	0.10	0.18	0.25
A_2	1.25	1.35	1.45	**A_3**	--	0.25	--
b_p	0.36	0.42	0.49	**c**	0.19	0.22	0.25
D	4.80	4.92	5.00	**E**	3.80	3.90	4.00
e	--	1.27	--	**H_E**	5.80	5.98	6.20
L	--	1.05	--	**L_p**	0.40	0.68	1.00
Q	0.60	0.65	0.70	**v**	--	0.25	--
w	--	0.25	--	**y**	--	0.10	--
Z	0.30	0.50	0.70	**θ**	0°		8°

Customer Service

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